

4D-Tracking with Digital SiPM-ICs

Exploring the Potential of CMOS SPAD Arrays

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HELMHOLTZ



Silicon Photomultipliers

State of the Art Solid State Photodetectors

The schematic diagram illustrates the PMT working principle. A light photon enters through an entrance window, striking a photocathode which emits a photoelectron. This electron is accelerated by a focusing grid and strikes a series of dynodes, causing a cascade of secondary electrons. The final electron avalanche is collected at the anode. The entire assembly is housed in a glass envelope under vacuum. A high voltage supply is connected to the photocathode and anode through a series of resistors. The output signal is taken from the anode through a load resistor R and a capacitor C.

PMT working principle

A photograph of a cylindrical PMT tube, labeled 'RCA ELECTRON TUBE', showing its glass envelope and metal base with pins.

PMT Example



The SiPM configuration schematic shows a Cathode (K) connected to a network of resistors Rq, which are connected to the Cathode and Anode (A). Each resistor is connected to a GM-APD (Geiger Mode Avalanche Photodiode) cell.

The SPAD Structure diagram shows a cross-section of the detector. It consists of a p⁺ substrate, a drift region, and a p-region. A high field region is formed by a p-n junction. The structure is covered by SiO₂ and Al. An electric field (E-field) is applied across the structure. The vertical axis is labeled x [μm] with values -0.2, -1.0, and W. The horizontal axis is labeled x [μm].

SiPM configuration

SPAD Structure

SiPM characteristic

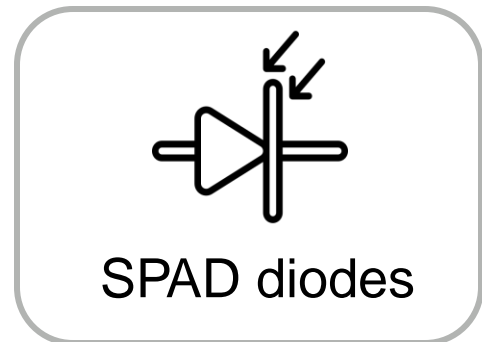
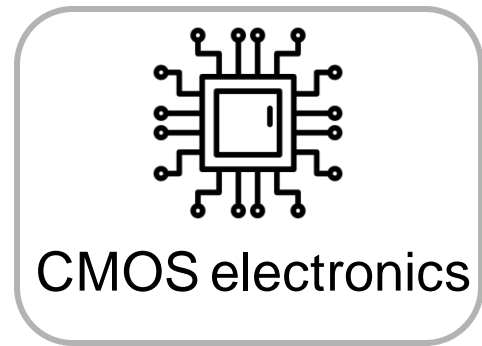
- Low voltage operation
- High and stable gain
- Excellent timing performance
- High photons sensitivity
- Insensitivity to magnetic fields
- Robustness

A photograph of a square SiPM chip, labeled '4x4 mm'. A magnifying glass shows a single pixel with a size of 10 μm.

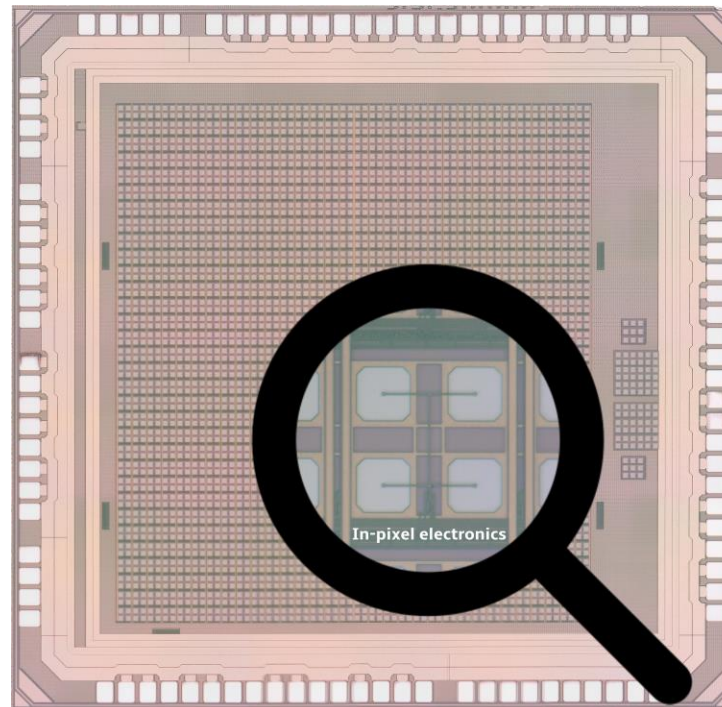
Example of SiPM

SiPM-IC Using Commercial CMOS Processes

Exploring SPADs in Foundries Process Design Kits



Digital SiPM integrated circuit (dSiPM)



DESY dSiPM in LFoundry 150 nm

Advantages

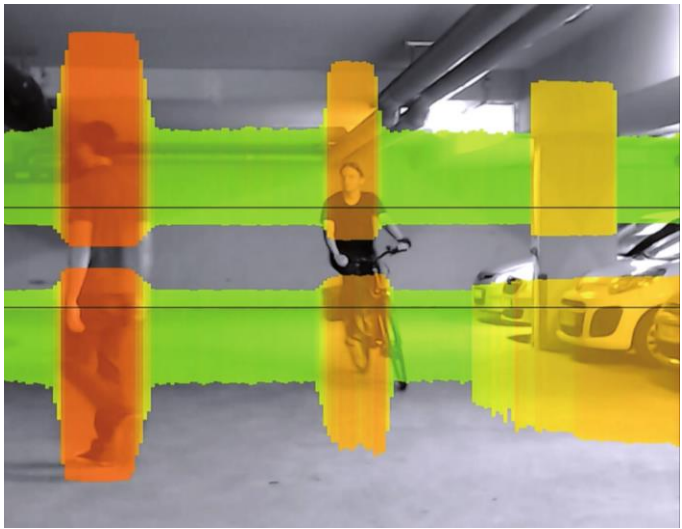
- large and fast signals
- Customized readout architectures
- Masking of noisy pixels
- Hitmap readout possible
- Simpler DAQ system
- Large volume production
- Low-cost implementation
- New possible applications

Drawbacks

- Processes not (yet) specialized
- Higher noise compared to SiPMs
- Reduced fill factor (electronics)

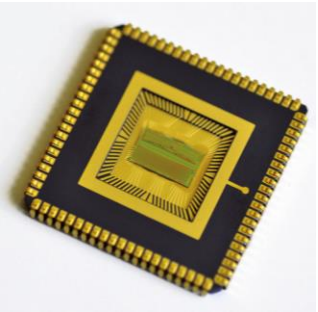
CMOS SPADs Applications

Commercial and HEP Examples

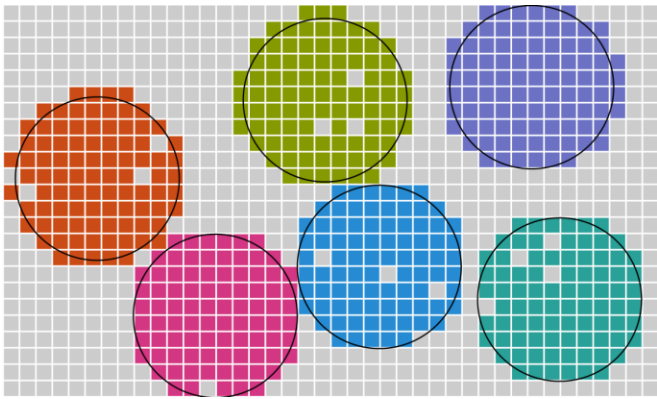


LIDAR & 4D-imaging

- Automotive
- Industry
- Security

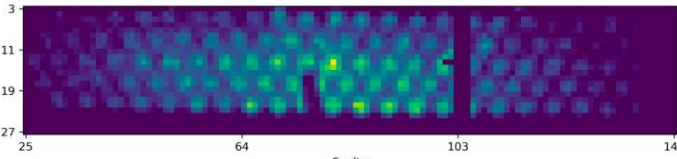
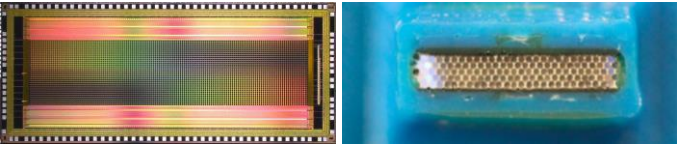


Images from: [Fraunhofer IMS](https://www.fraunhofer-ims.de/)

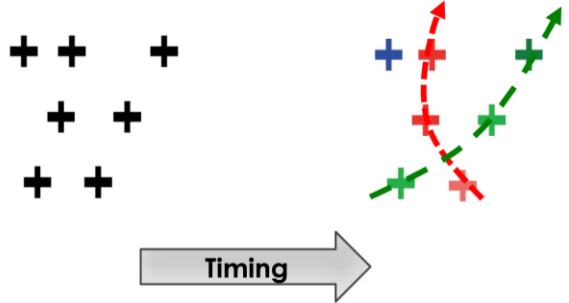


Scintillating fibers readout

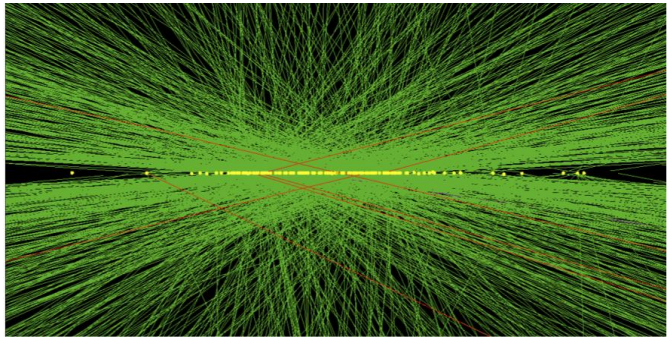
- Calorimetry, tracking



<https://doi.org/10.1016/j.nima.2022.167033>



Timing



4D-Tracking of charged particles?

- MIPs tracking and timing

<https://dx.doi.org/10.1088/1361-6633/aa94d3>

dSiPM as Possible 4D-Tracker Candidate

Beyond Photon Detection Applications

MIP detection with analog devices

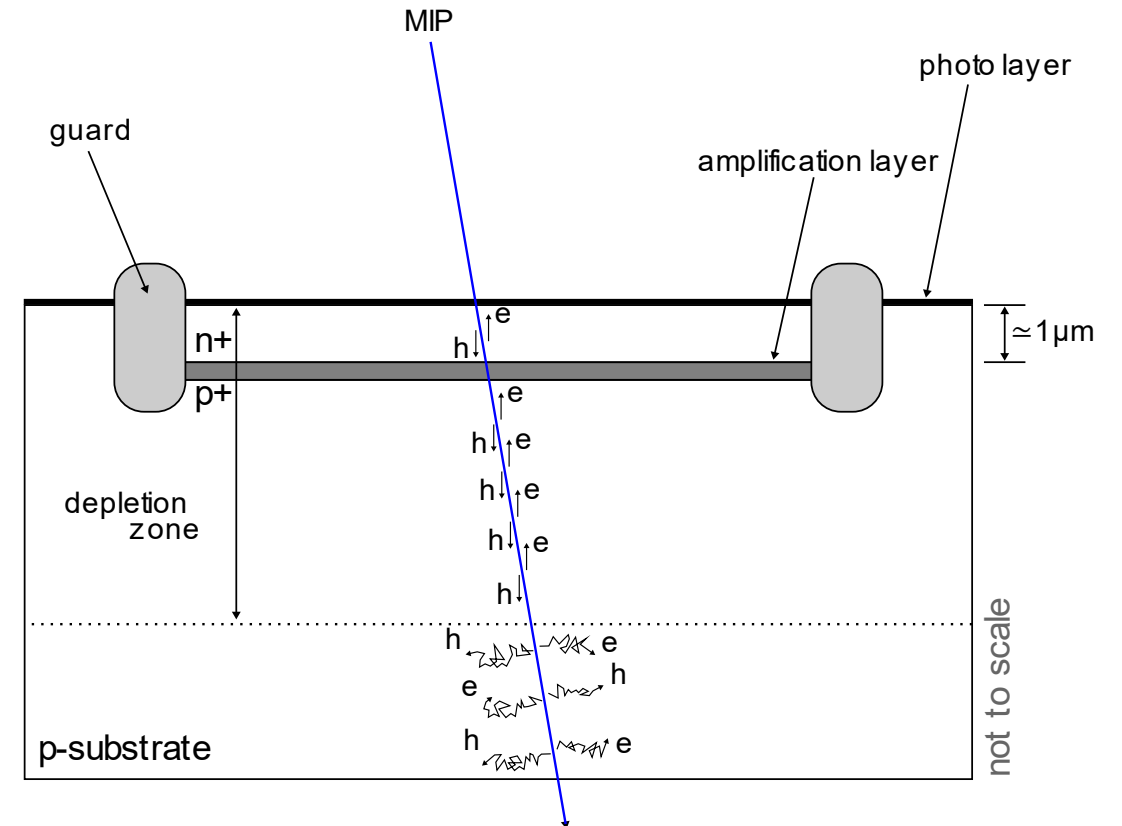
- SPAD/SiPMs already proved to be good MIPs detectors [1] [2]
- Excellent intrinsic timing performance $O(10 \text{ ps})$
- Photon detection is still possible (multipurpose detector)

Using CMOS dSiPM

- On-chip data processing and digitalization
- Tracking-like detector architecture possible
- High granularity with $O(10 \mu\text{m})$ spatial resolution
- Large area/volume production possible

Drawbacks

- Efficiency is limited by the fill factor
- High DCR compared to standard pixel detectors
- No distinction between signal and noise



MIP interaction in a SPAD

DESY dSiPM Prototype

ASIC in LF 150 nm CMOS

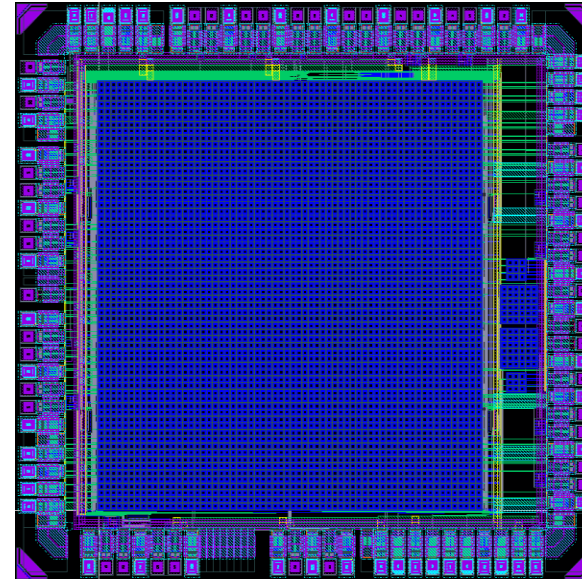
Layout

- In LFoundry 150 nm CMOS technology
- Main matrix: 32 x 32 pixels (4 SPADs per pixel)
- Sensor area: 2.2 x 2.4 mm²
- Test structures in the chip periphery

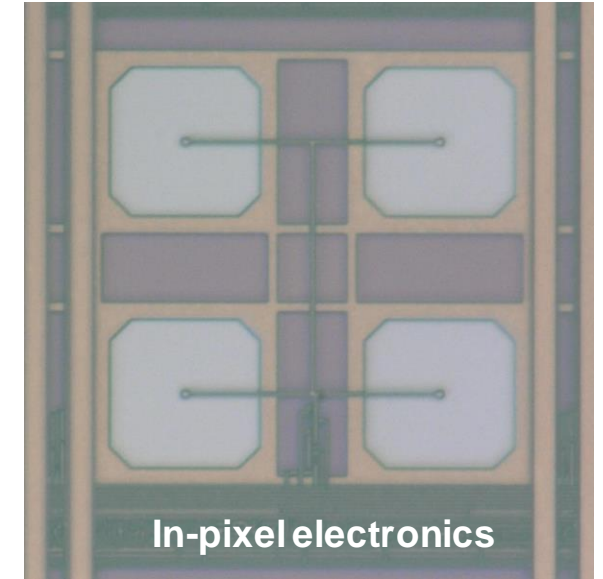
Features

- Full hit matrix readout and timing measurements
- 4 x 12-bit Time to Digital Converters with ~95 ps bins
- Pixel masking & 2-bit in-pixel hit counting
- Quenching can be tuned (quenching transistor)
- In chip trigger logic
- Readout is frame-based (3 MHz frame rate)
- Versatile Caribou DAQ system is used for biasing & readout

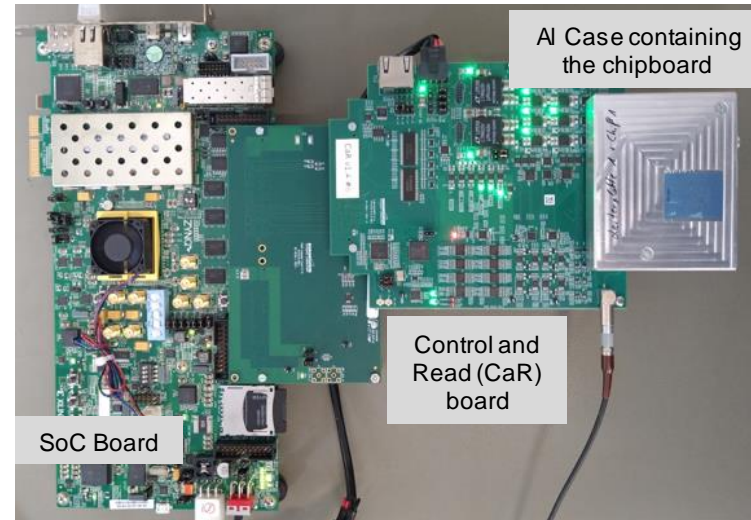
For details: [I. Diehl et al 2024 JINST 19 P01020](#)



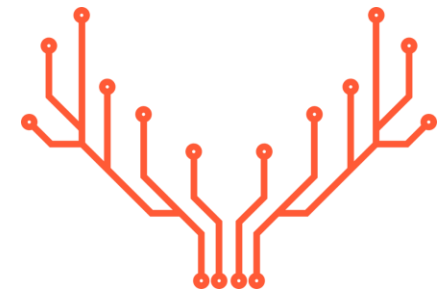
ASIC design of the DESY dSiPM



DESY dSiPM pixel picture (69.6 x 76 μm²)



DAQ System



Caribou DAQ system

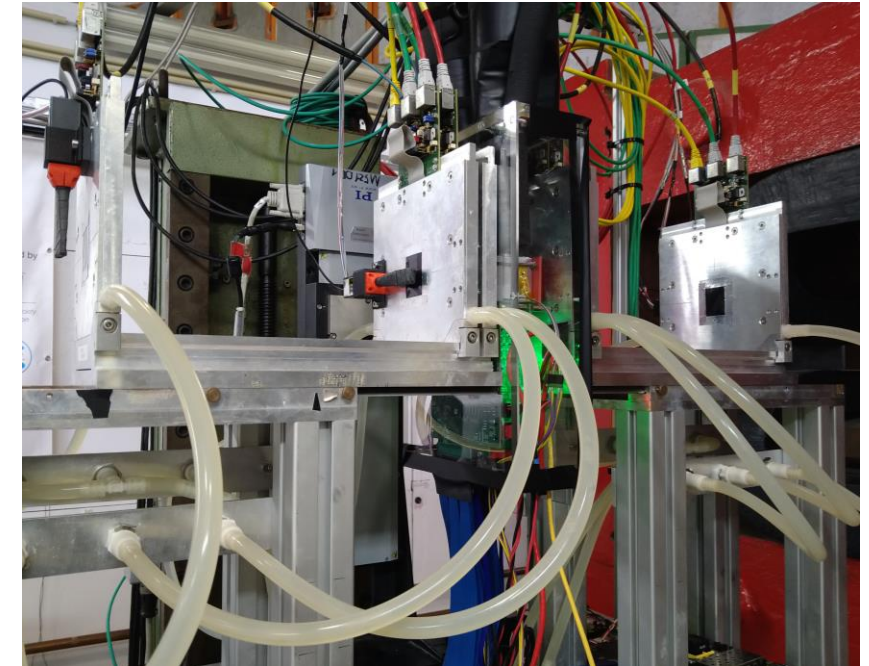
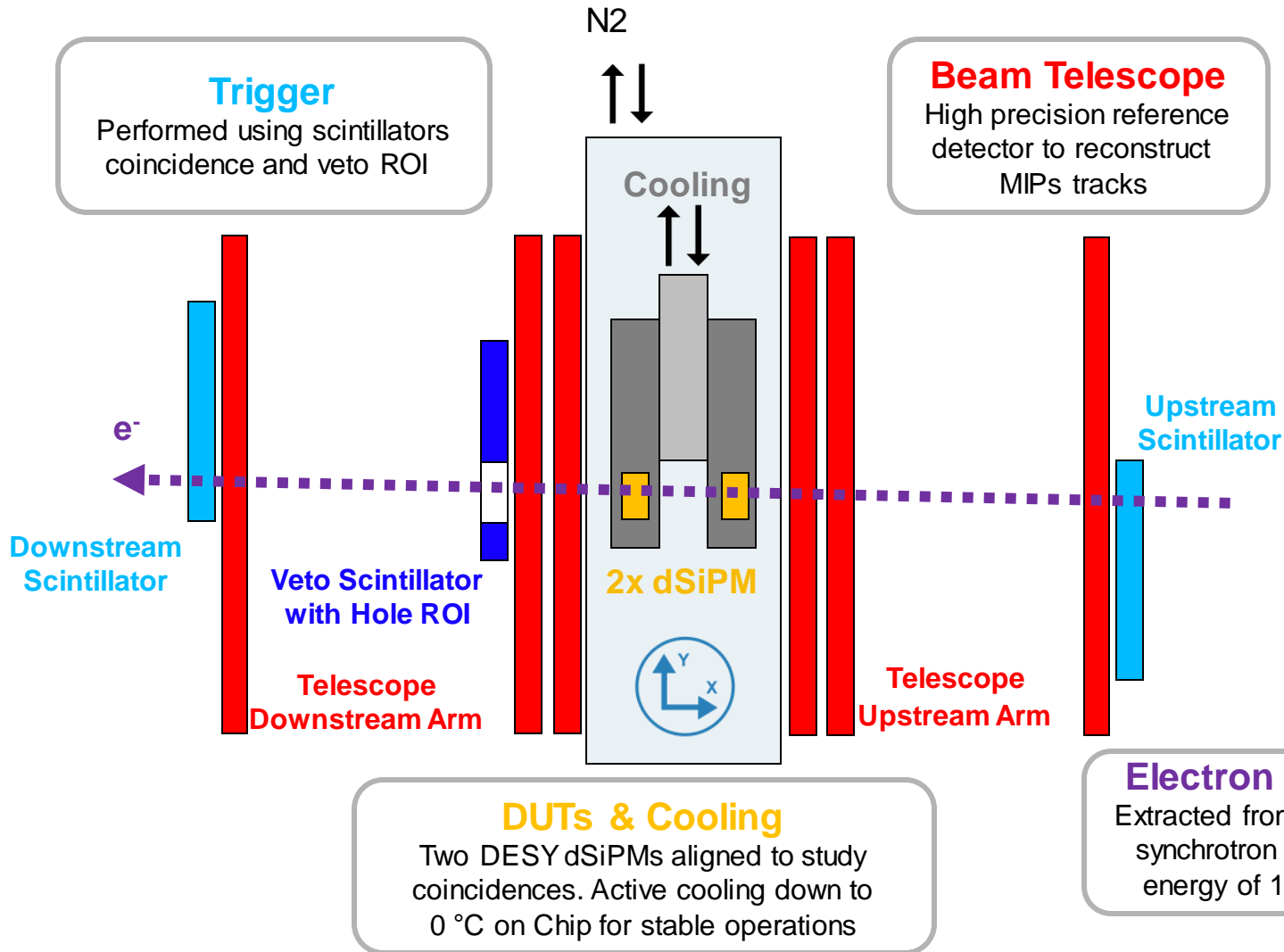
Fast & low cost implementation of solid state detector prototypes

<http://dx.doi.org/10.22323/1.370.0100>

<https://gitlab.cern.ch/Caribou/>

DESY dSiPM Test Beam

Device Treated as a Particle Detector



DESY dSiPM test beam setup

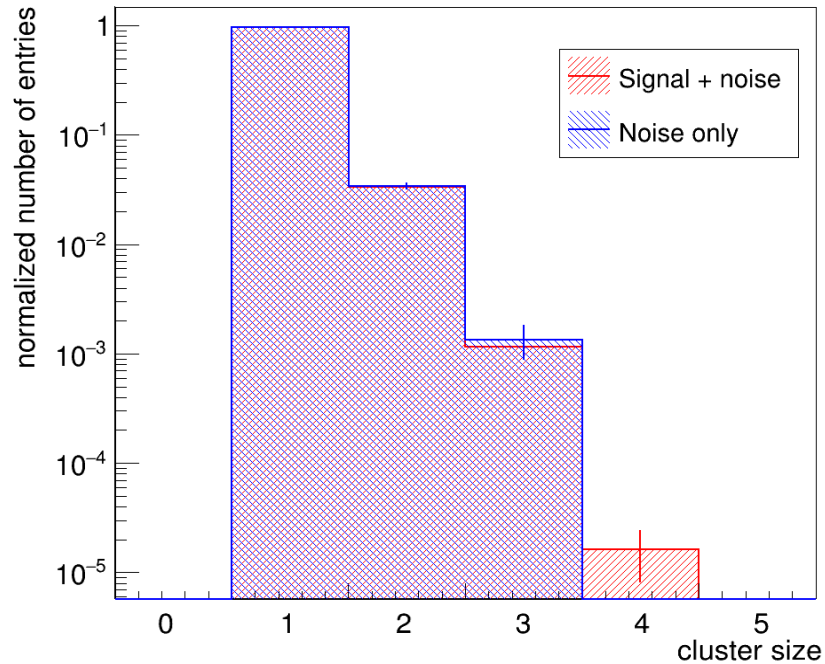


- **EUDAQ** framework and AIDA TLU used for data acquisition and synchronization of devices.
- **Corryvreckan** Framework used for test beam data reconstruction and analysis

DESY dSiPM Spatial Properties

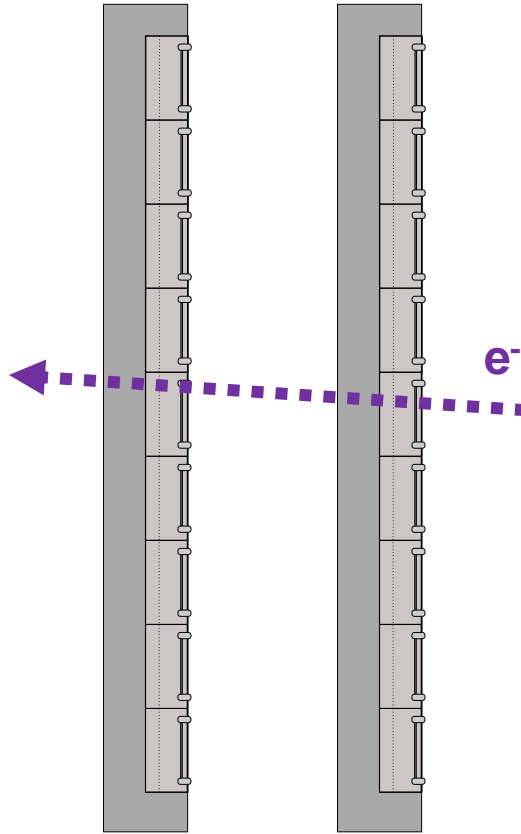
Direct MIP Detection (Only Silicon)

Associated cluster size



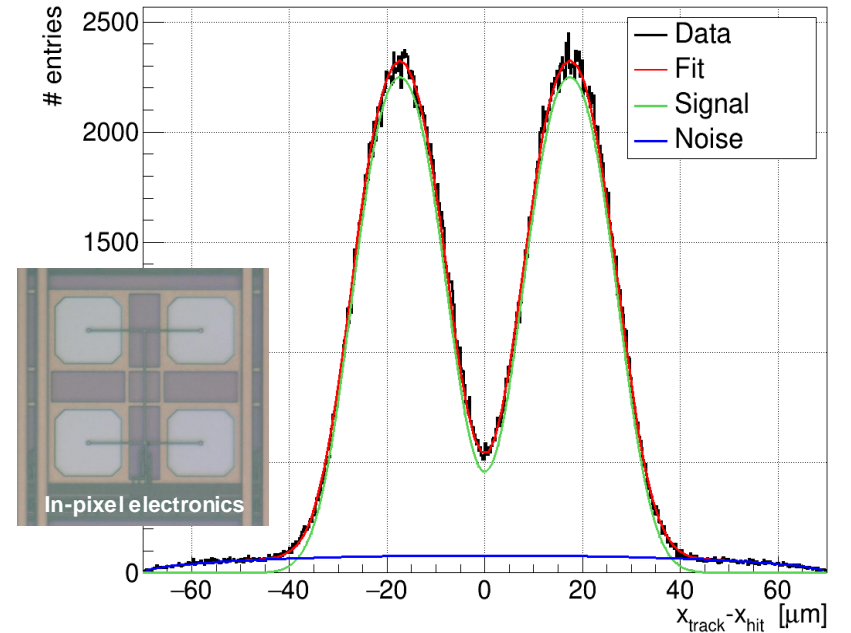
- Cluster size mainly one (log scale in figure)
- Signal and noise have the same cluster size
- Events with larger clusters due to crosstalk

dSiPM_1 dSiPM_0



MIP detection with bare silicon

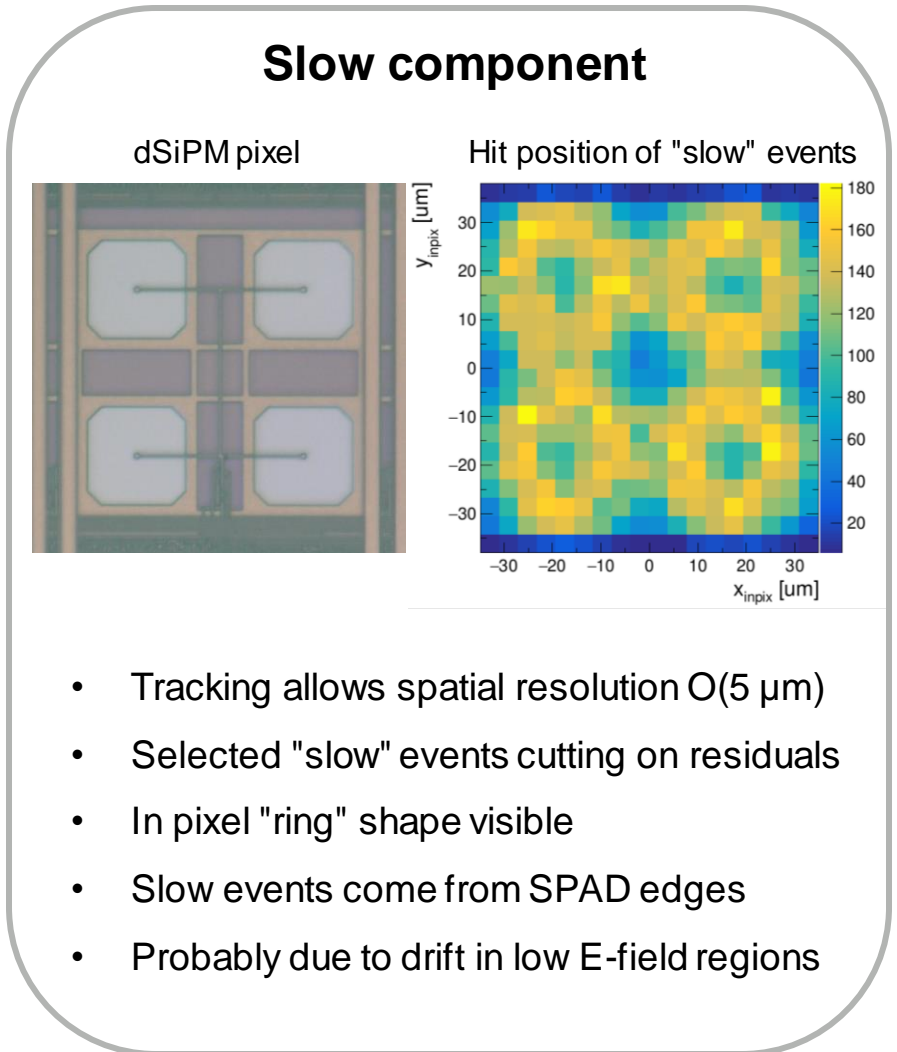
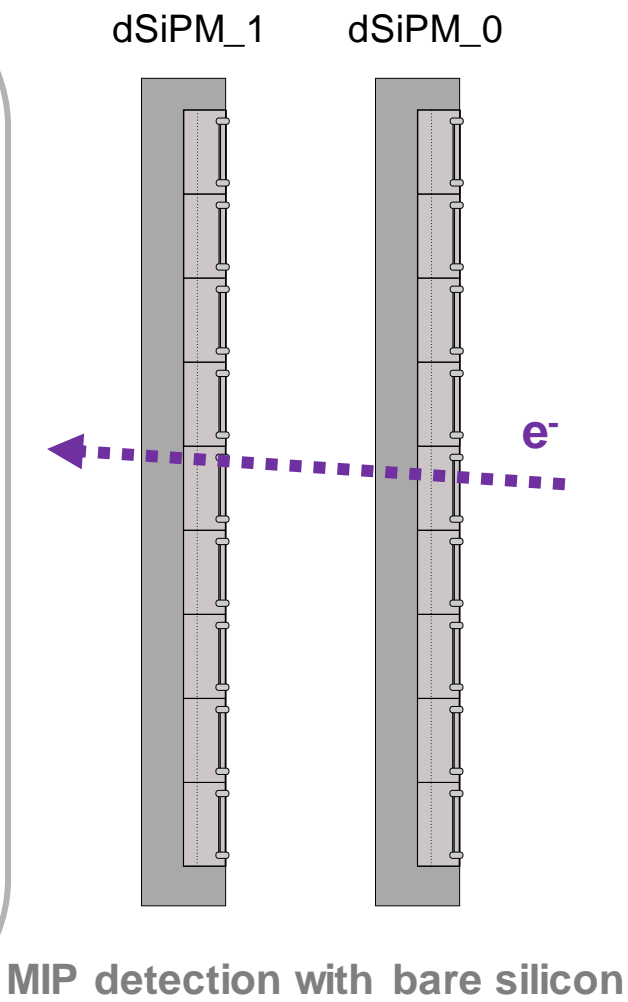
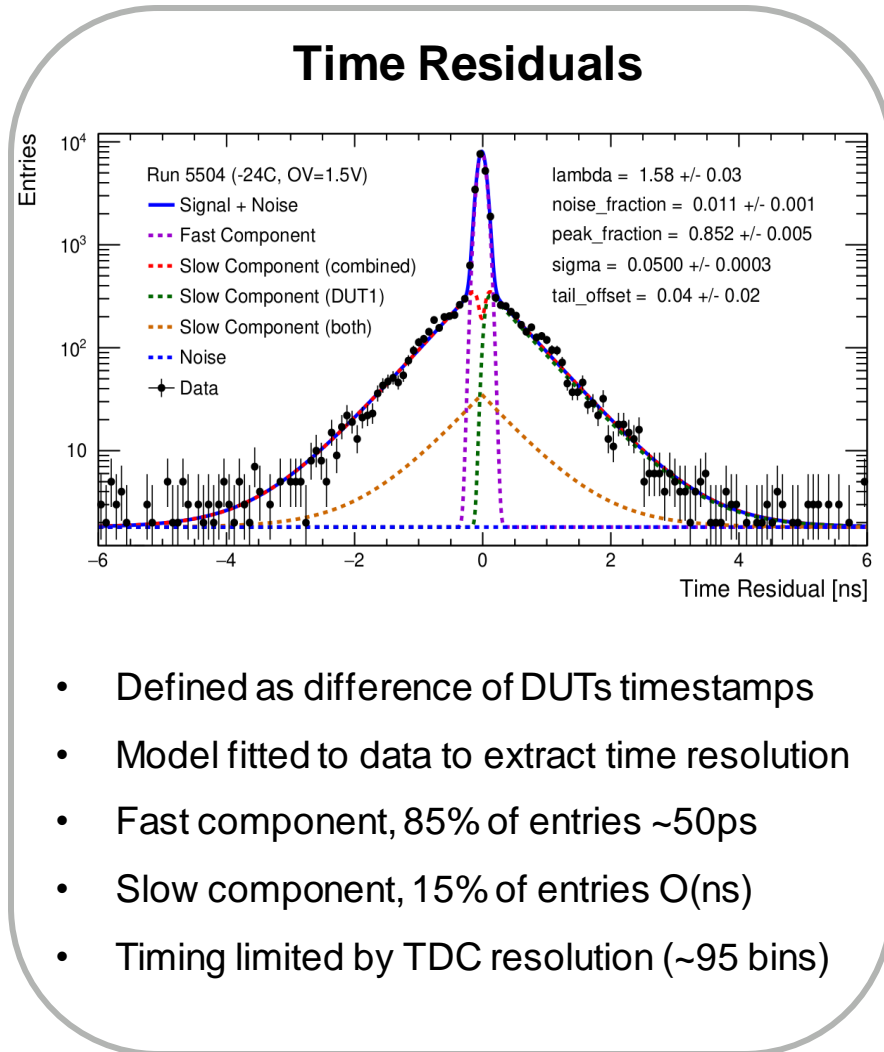
Spatial Residuals



- Distance between dSiPM hit and track
- Shape due to in-pixel 4 SPADs structure
- Spatial resolution $O(20 \mu\text{m})$

DESY dSiPM Timing

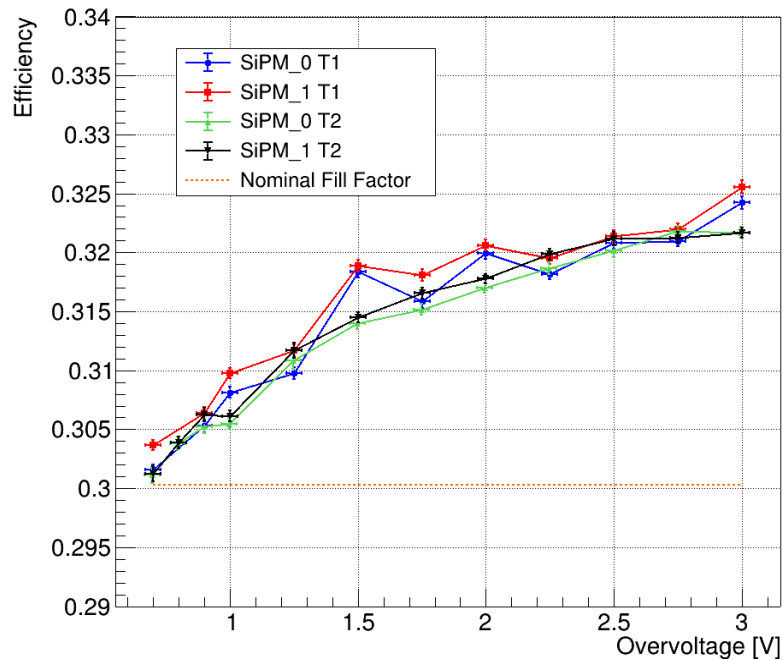
Direct MIP Detection (Only Silicon)



DESY dSiPM Efficiency

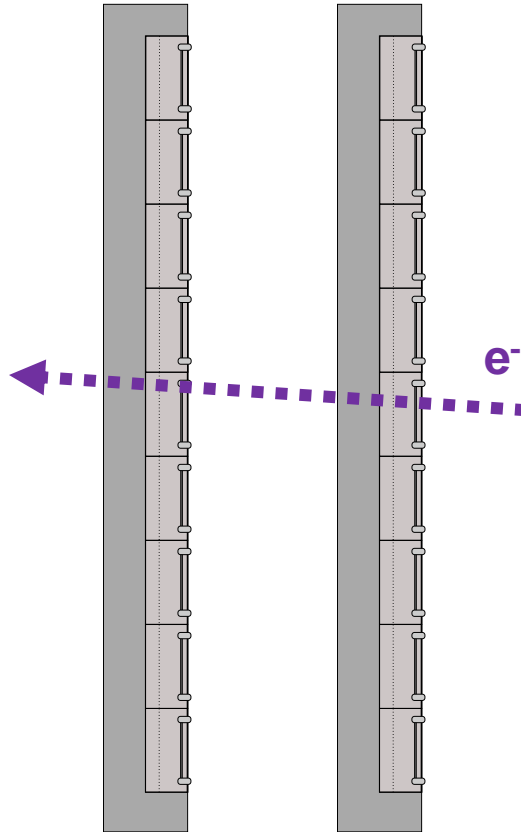
Direct MIP Detection (Only Silicon)

Efficiency VS overvoltage



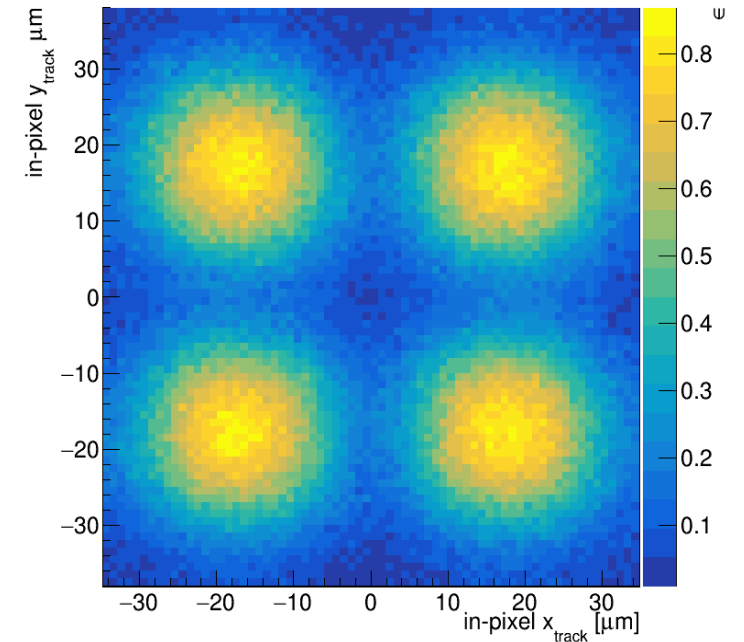
- Efficiency compatible with fill factor (~30%)
- Small overvoltage dependence
- No temperature/sample dependence

dSiPM_1 dSiPM_0



MIP detection with bare silicon

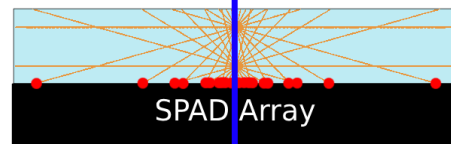
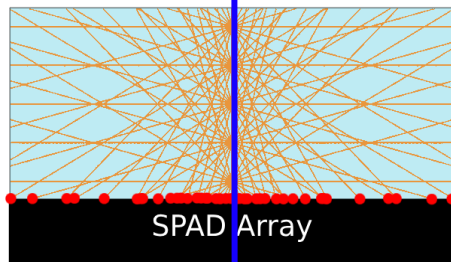
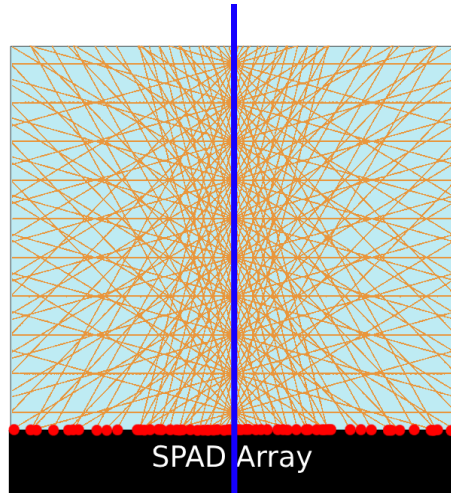
In-pixel efficiency



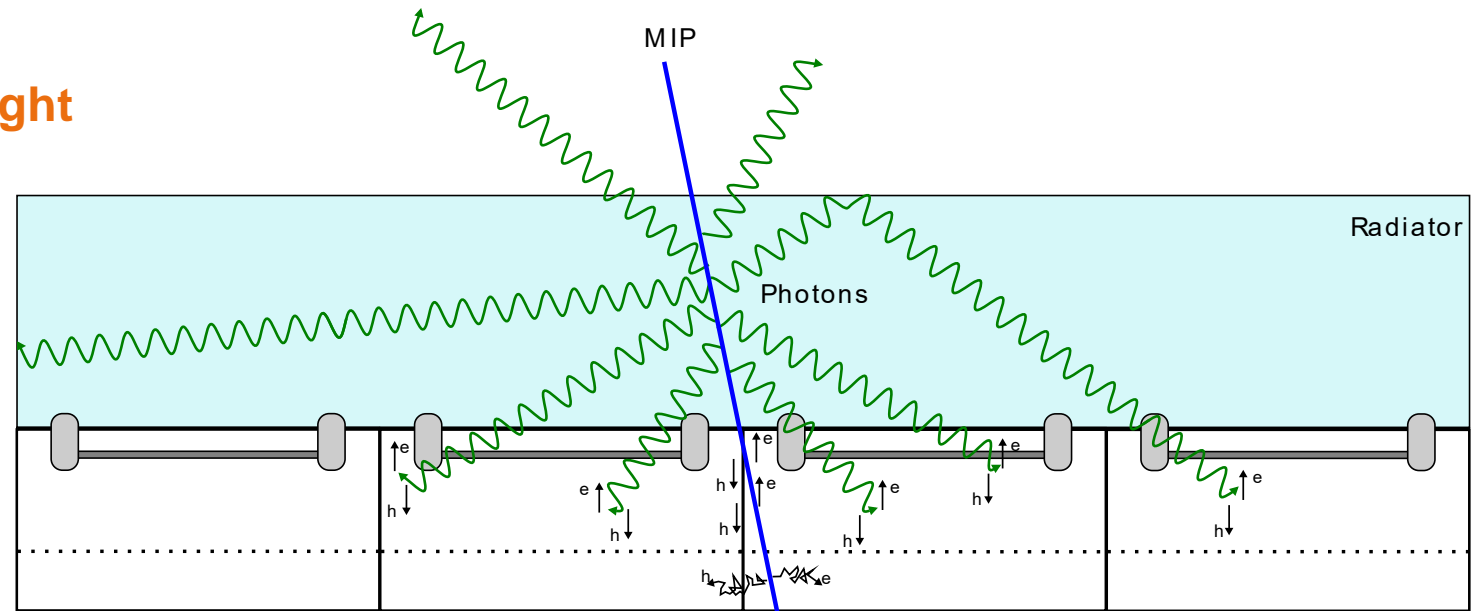
- Image resolution limited by tracking
- Maximum efficiency in the SPAD centre
- Lower efficiency in SPAD edges

Thin Radiator Concept

Detecting Cherenkov & Scintillation Light

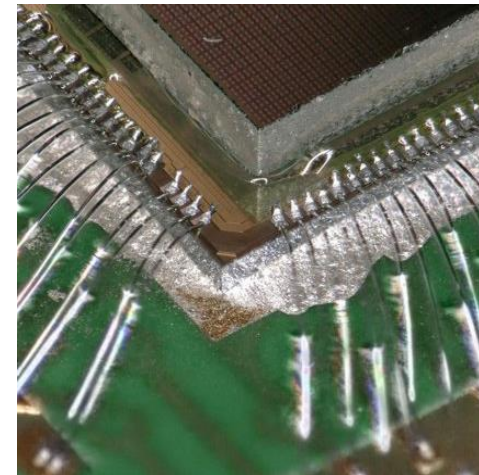


Not a simulation

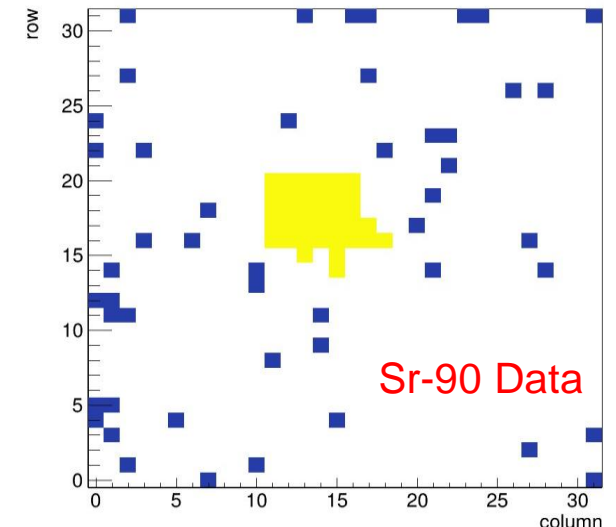


DESY dSiPM + thin LYSO

- Overcome efficiency limit
- Reduce noise contamination (large signals for MIP events)
- Preserve good spatial resolution
- Concept already explored using analog SiPM [1] [2] [3]
- Three sample assembled with 100, 200 & 500 μm thick LYSO



Thin LYSO glued on DESY dSiPM

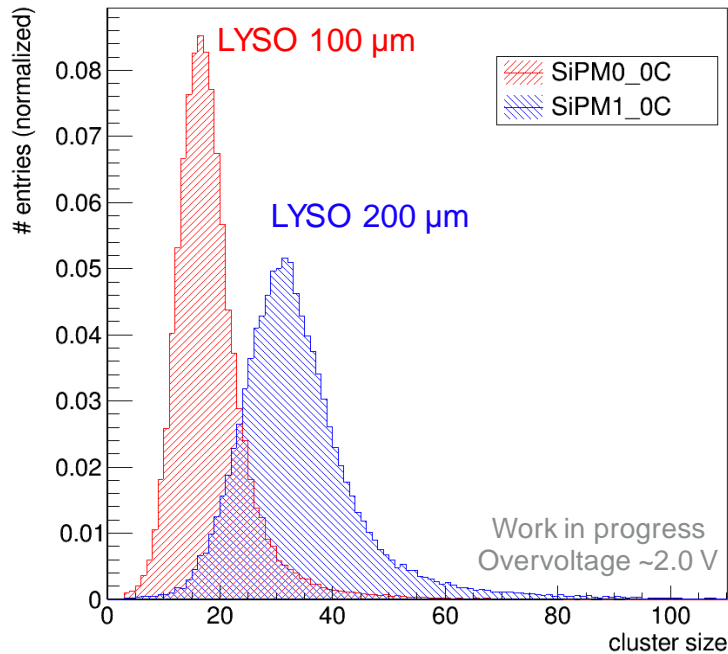


dSiPM + 200 μm LYSO MIP hit map

DESY dSiPM + Thin LYSO

Cluster Size, Signal & Noise with Different Tagging

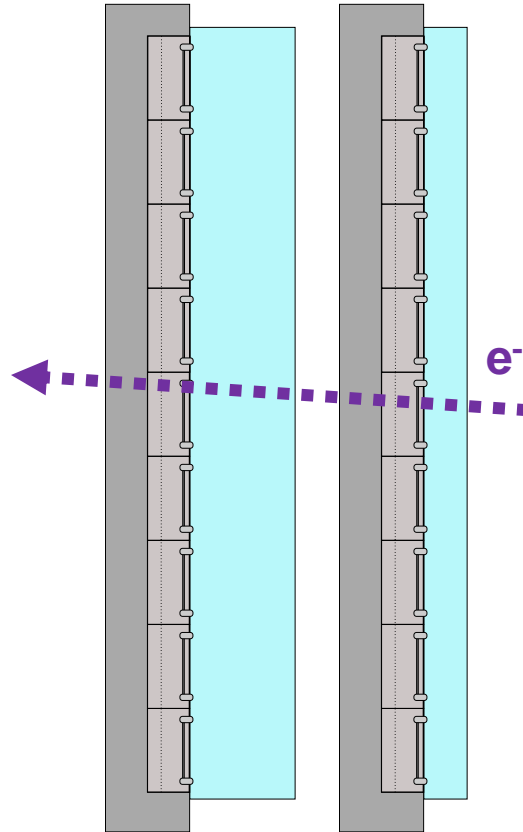
MIP events cluster size



- Large cluster size for MIP events
- DCR hits (1 or 2 pixels) can be filtered
- Very low noise with threshold on clusters

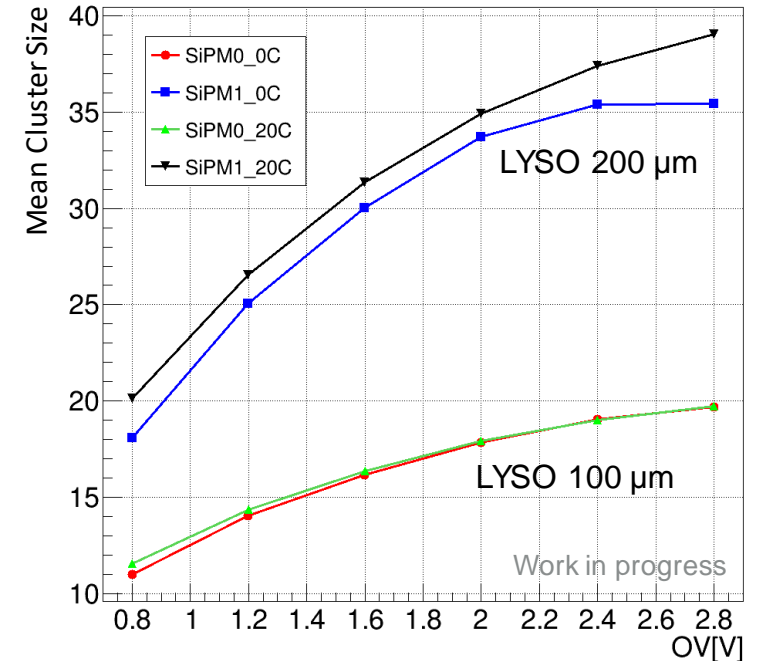
dSiPM_1
200 μm LYSO

dSiPM_0
100 μm LYSO



MIP detection with thin radiator coupling

Cluster size VS overvoltage

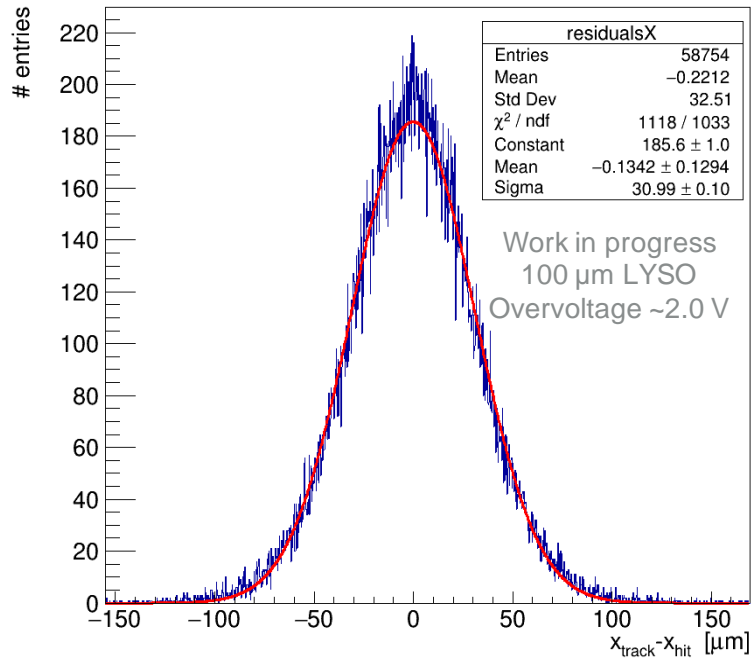


- The thicker the LYSO, the larger the cluster
- Overvoltage dependence due to PDE increase
- Small temperature (DCR) dependence

DESY dSiPM + Thin LYSO

Spatial Residuals, Good Spatial Performances Preserved

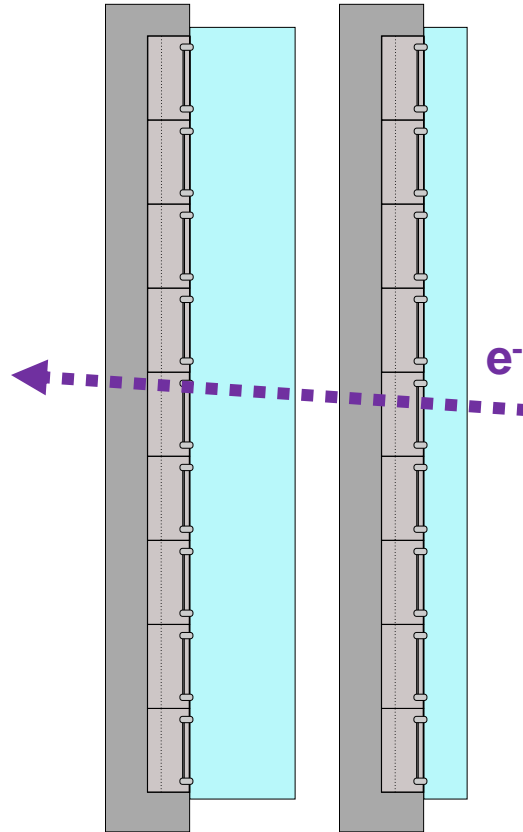
Spatial Residuals



- In-pixel structure not visible
- Gaussian shape
- Good spatial resolution preserved

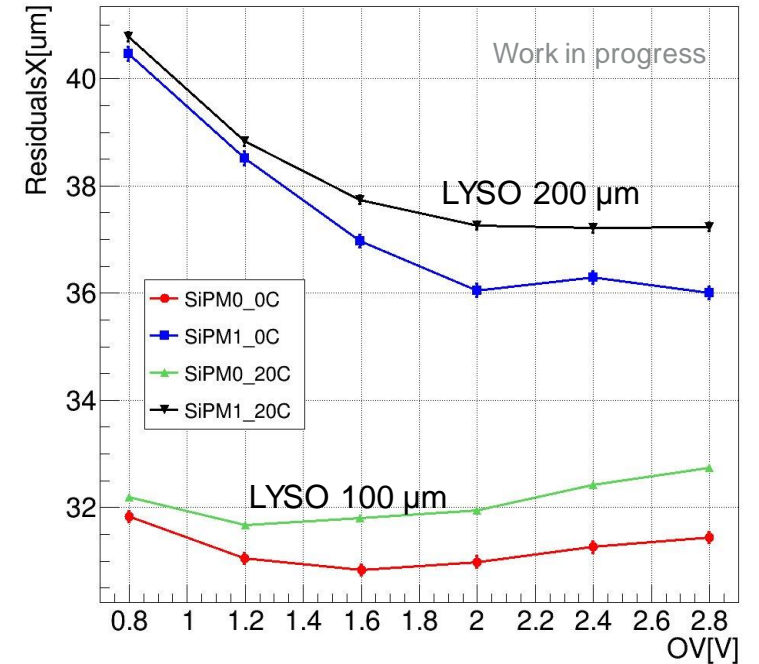
dSiPM_1
200 μm LYSO

dSiPM_0
100 μm LYSO



MIP detection with thin radiator coupling

Residuals VS overvoltage

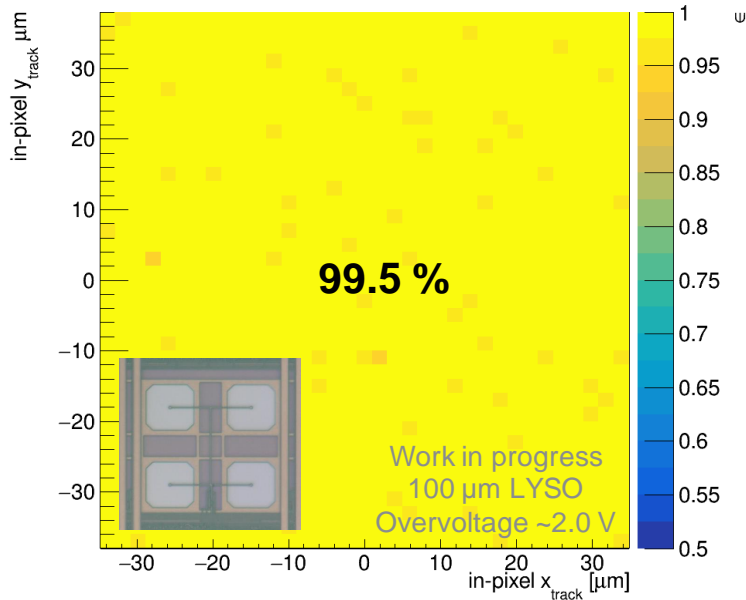


- Thinner LYSO has better spatial resolution
- Sigma ~32 μm (100μm LYSO) and ~38 μm (200μm LYSO)
- Small OV & temperature dependence

DESY dSiPM + Thin LYSO

Efficiency & Timing Performances

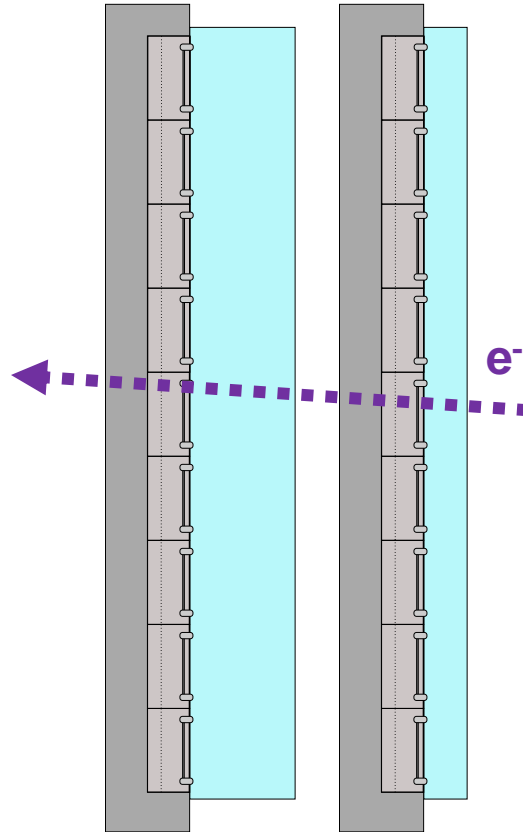
In-pixel Efficiency



- Uniform in-pixel efficiency (SPADs position no longer visible)
- From $\sim 33\%$ (bare silicon) to $>99\%$ using Thin LYSO coupling
- No OV or temperature dependence

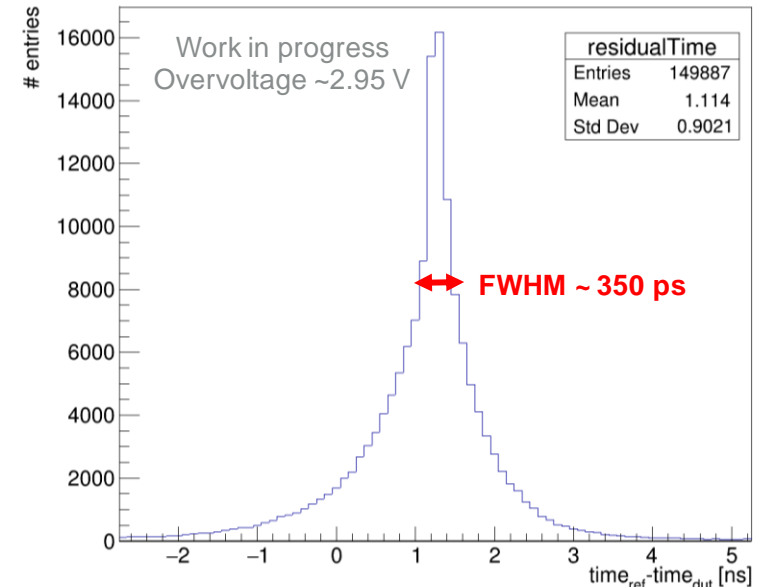
dSiPM_1
200 μm LYSO

dSiPM_0
100 μm LYSO



MIP detection with thin radiator coupling

Time residual distribution



- Fast time residuals core with FWHM ~ 350 ps
- Important fraction of event in residuals tails
- Probably due to LYSO timing property
- Faster radiators may improve timing

Summary & Outlook

dSiPM as 4D-Tracking Candidate

CMOS dSiPMs

- Combination of SPAD and CMOS electronics in the same silicon die opens new application possibilities
- Reduction of complexity & cost especially for large volumes

DESY dSiPM & MIPs 4D-Tracking

- dSiPM can be a possible candidate technology for 4D-tracking
- Spatial resolution down to $\sim 20 \mu\text{m}$ and $\sim 50 \text{ ps}$ system timing
- Efficiency $>99\%$, very low noise rate using thin LYSOs

CMOS dSiPMs R&D Potential

- dSiPM can play an important role in future HEP detector systems
- CMOS dSiPMs are a "young" technology, promising R&Ds ongoing
- Any new idea of possible HEP application is welcome

DESY dSiPM 4D-Tracking Performances

	dSiPM	dSiPM+LYSO
Signal Cluster Size	~ 1	10 – 40
Spatial Resolution	$\sim 20 \mu\text{m}$	$\sim 35 \mu\text{m}$
Efficiency in MIP detection	$\sim 33 \%$	$> 99 \%$
Noise Rate	O(MHz)	O(Hz)*
Time Resolution	$\sim 50 \text{ ps}$	$< 1 \text{ ns}^{**}$

* While cutting on cluster-size

** Currently under investigation

Thank you. ■

References:

I. Diehl et al, Monolithic MHz-frame rate digital SiPM-IC with sub-100 ps precision and 70 μm pixel pitch

S.Lachnit, Time Resolution of a Fully-Integrated Digital Silicon Photo-Multiplier

F.Feindt et al, The DESY digital silicon photomultiplier: Device characteristics and first test-beam results

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1C, O1.331, ATLAS



The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF).

DESY dSiPM ASIC

More Details in Reference Publication

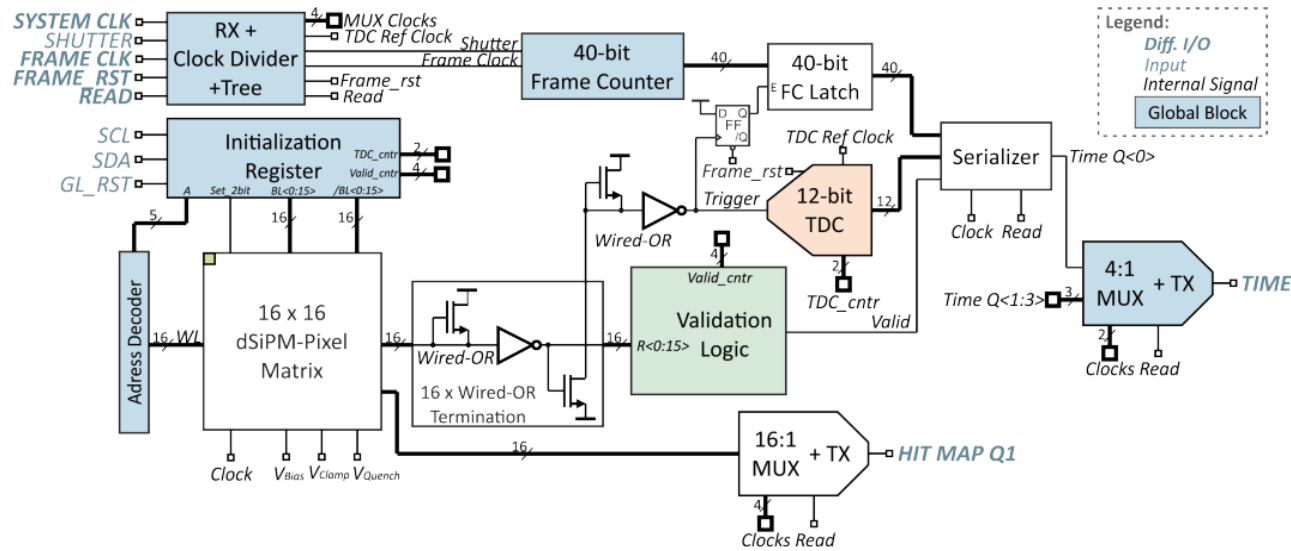


Figure 2. Quadrant block diagram.

From: [I. Diehl et al 2024 JINST 19 P01020](#)

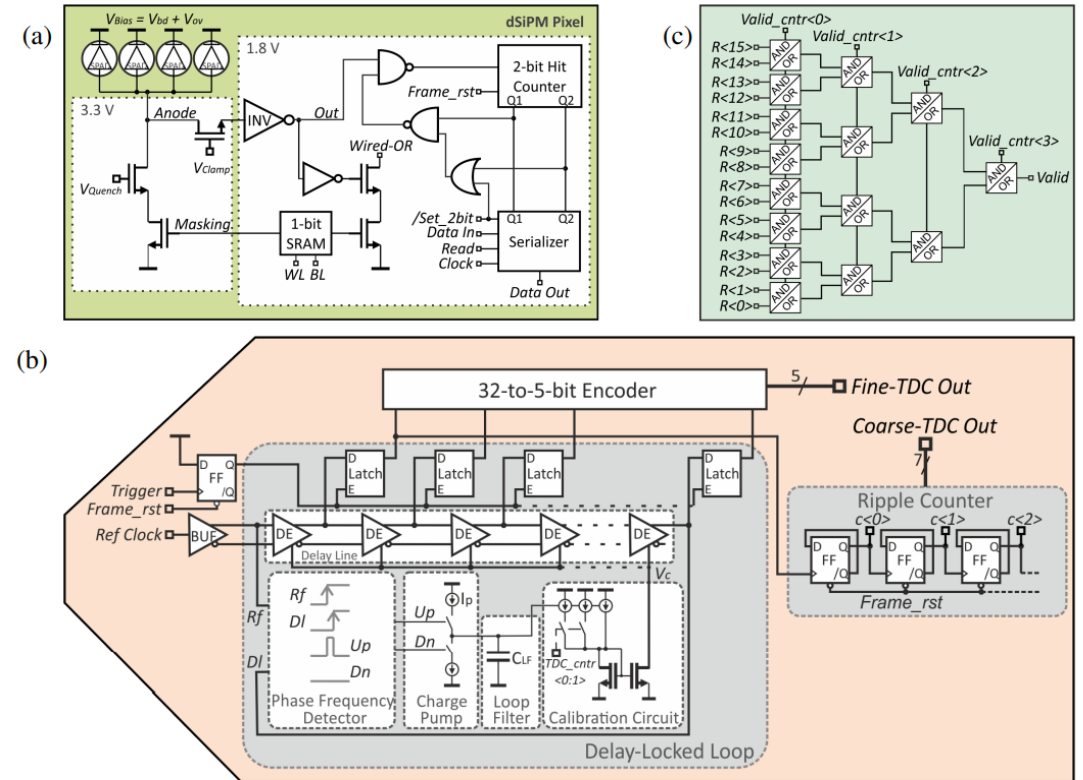
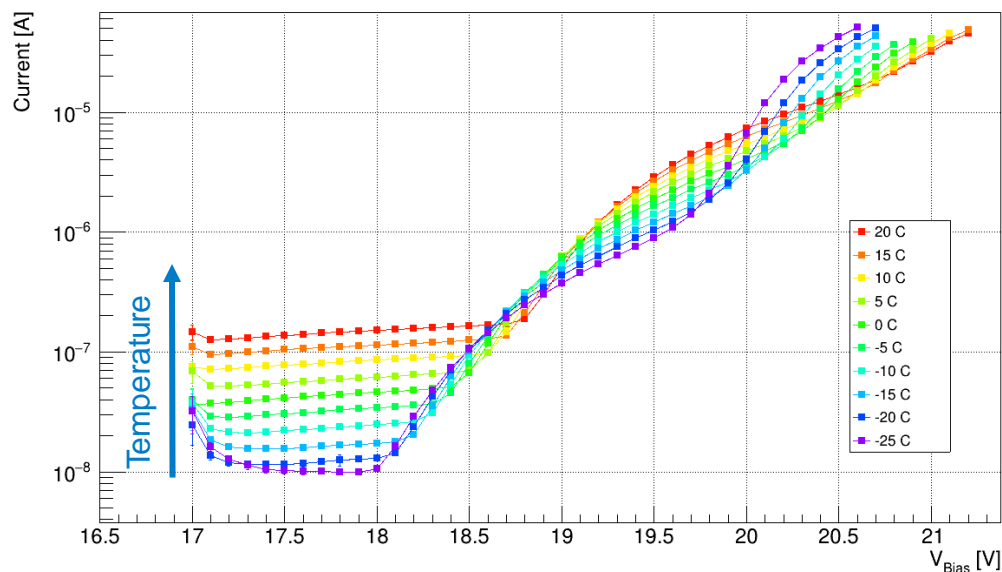


Figure 3. Simplified equivalent circuits of: (a) the dSiPM pixel, (b) the TDC, and (c) the validation logic.

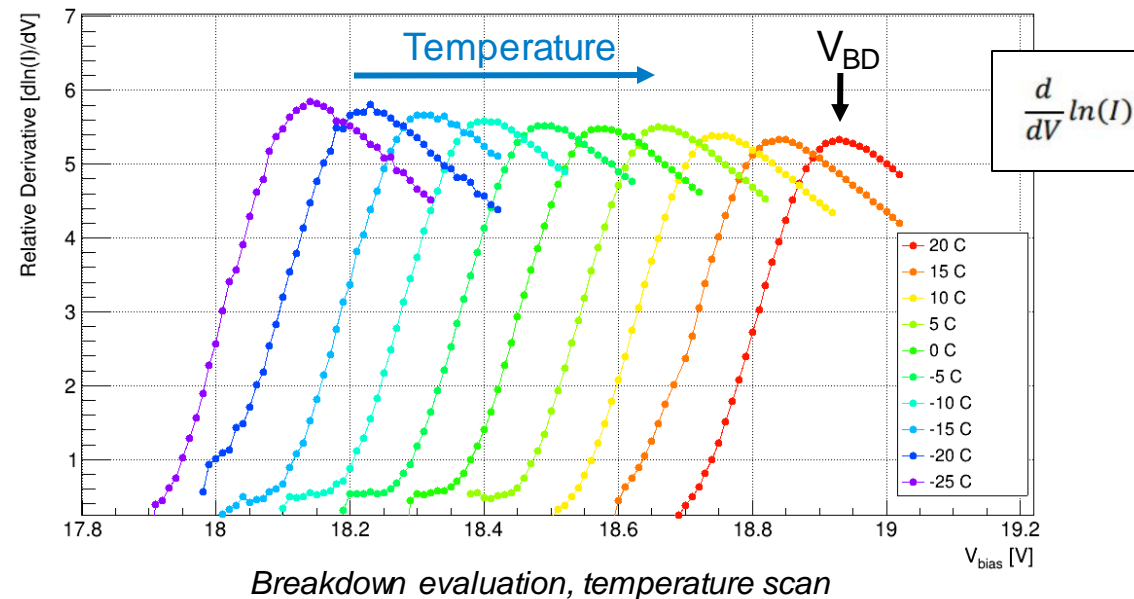
IV Curves & Dark Count Rate

Basic Chip Characterization

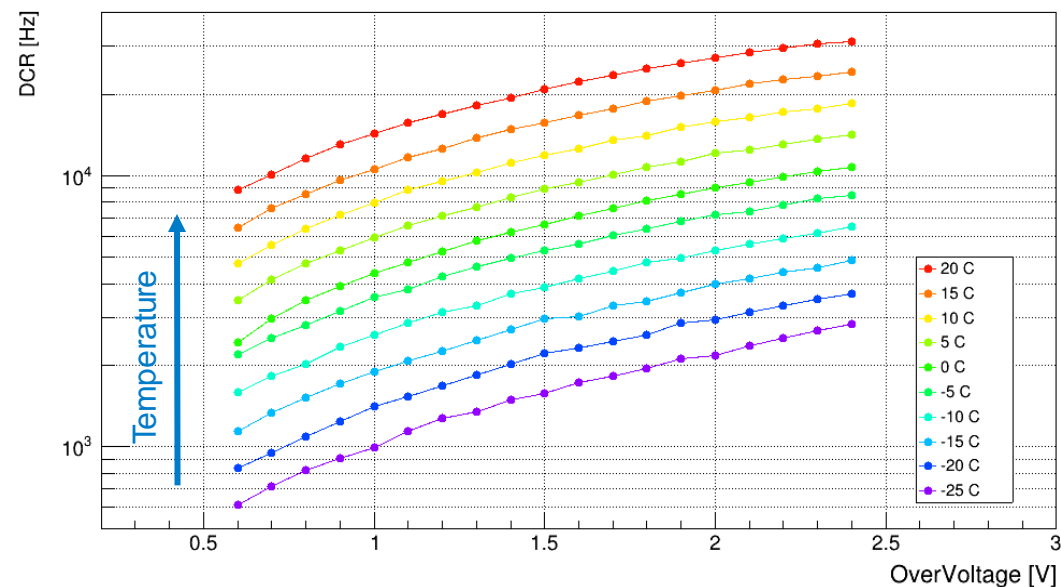
- Detailed characterization performed on several samples (Chip4 shown in figures)
- IV & Dark Count Rate studies performed with controlled **temperature** (from -25 to 20 °C) and **humidity** (~ 0 %) in a dark environment
- Measurements compatible with expectations



IV curves (full matrix), temperature scan



Breakdown evaluation, temperature scan



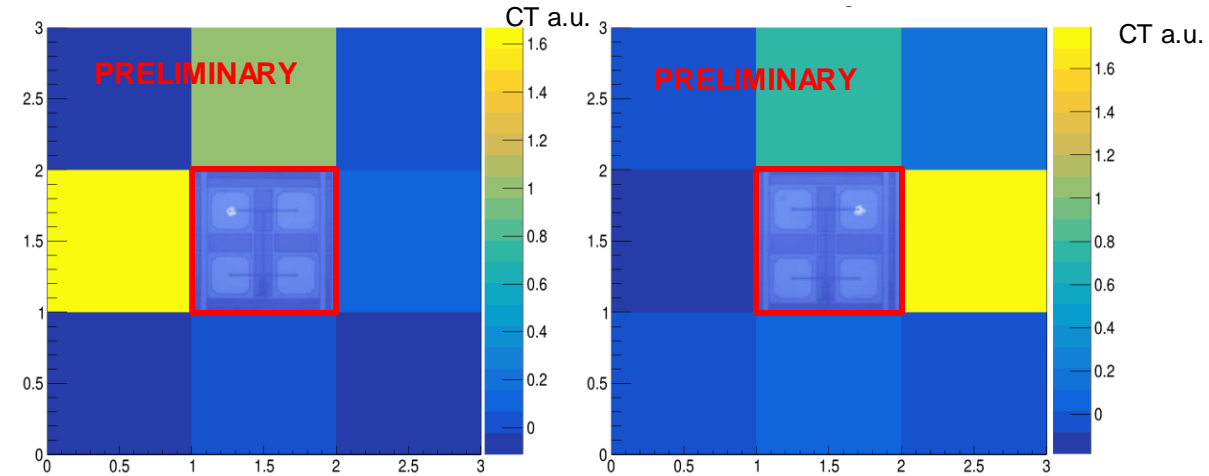
Dark Count Rate (per pixel), temperature scan

DESY dSiPM Characterisations

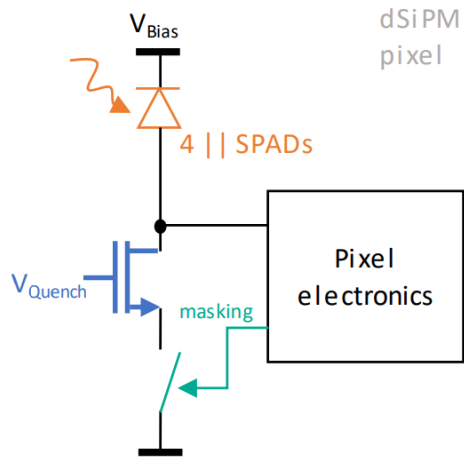
Exploring the Potential of Digital SPADs

Studies possible thanks to digital features

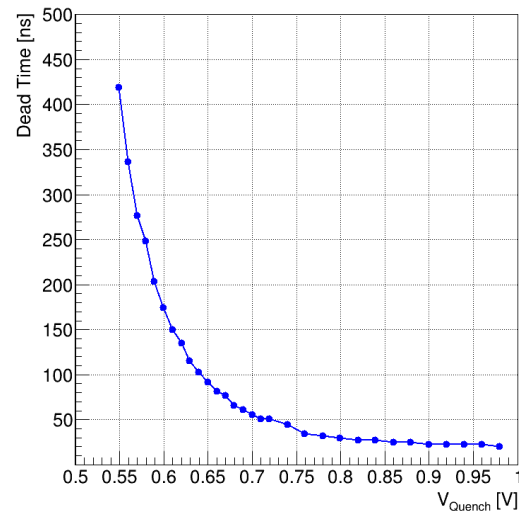
- Effect of **quenching** transistor tuning in sensor response
- Pixel **masking**: effect on IV and DCR reduction
- Pixel **crosstalk** characterisation: studying the correlation between avalanche position and CT probability in neighbours



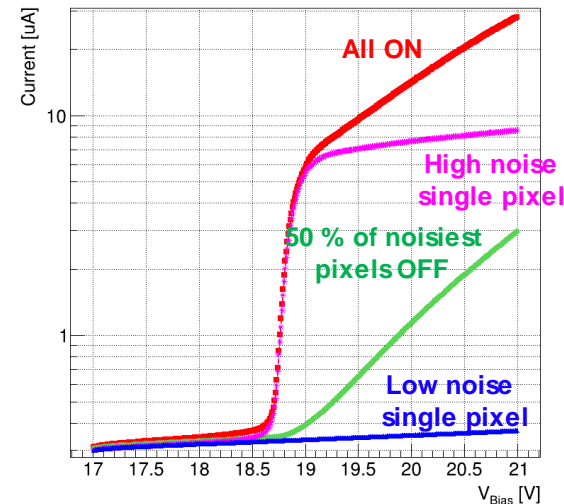
Crosstalk studies as function of avalanche position



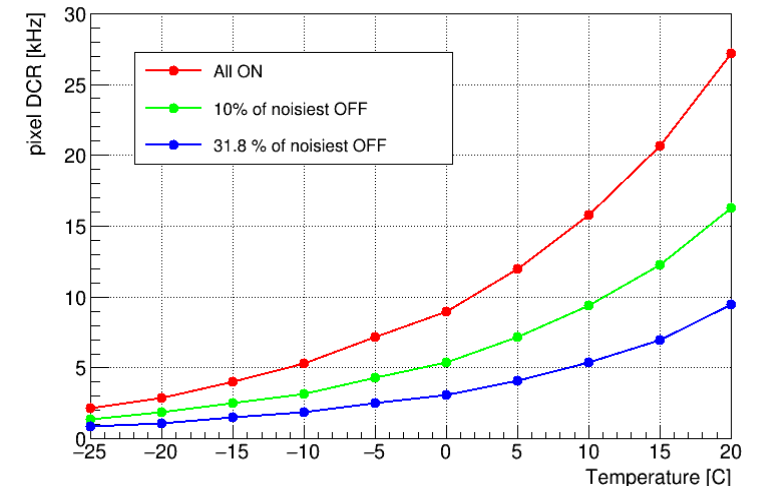
Pixel circuit



Dead time vs V_{Quench}



IVs with different masks



DCR with different masks (2 OverVoltage)

DAQ System in Test Beam

AIDA TLU Core

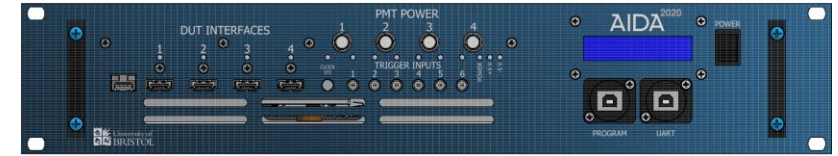


<https://doi.org/10.1140/epjt/s40485-016-0033-2>

Scintillators
& PMTs

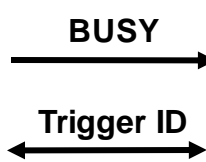


NIM Logic

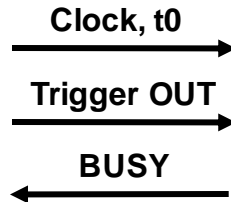


<https://doi.org/10.1088/1748-0221/14/09/P09019>

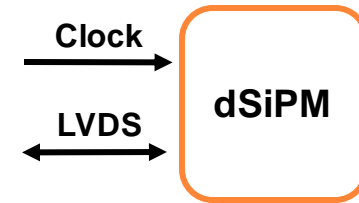
EUDET TELESCOPE
(6 x Mimosa 26)



AIDA Trigger Logic Unit
"Aida Mode"



Caribou DAQ



dSiPM

Event Timestamp
& Trigger ID



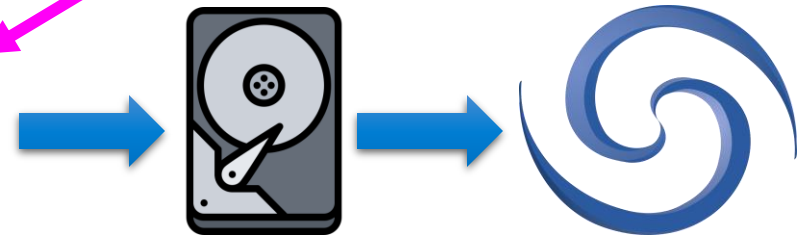
dSiPM Hitmap
& Timestamp

<http://dx.doi.org/10.22323/1.370.0100>

Telescope
Hitmap



<https://github.com/eudaq>



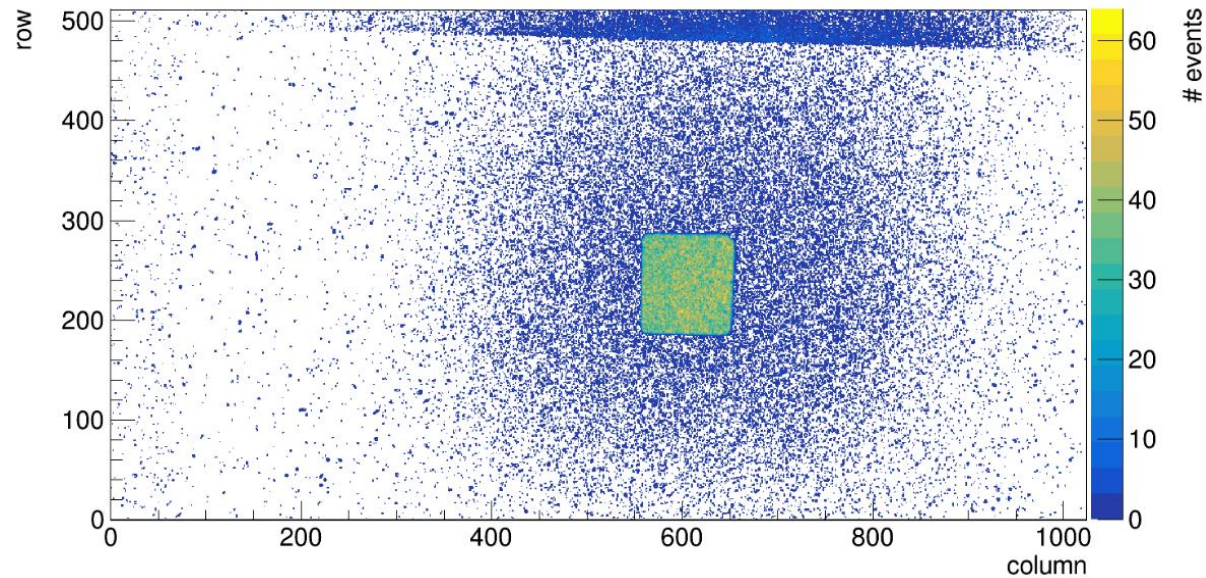
<https://gitlab.cern.ch/corryvreckan/corryvreckan>

DESY II Test Beam Setup

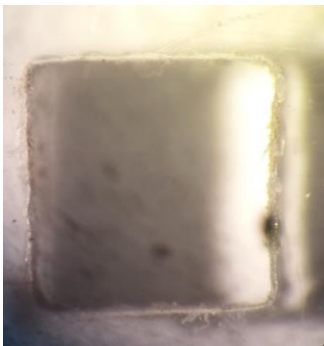
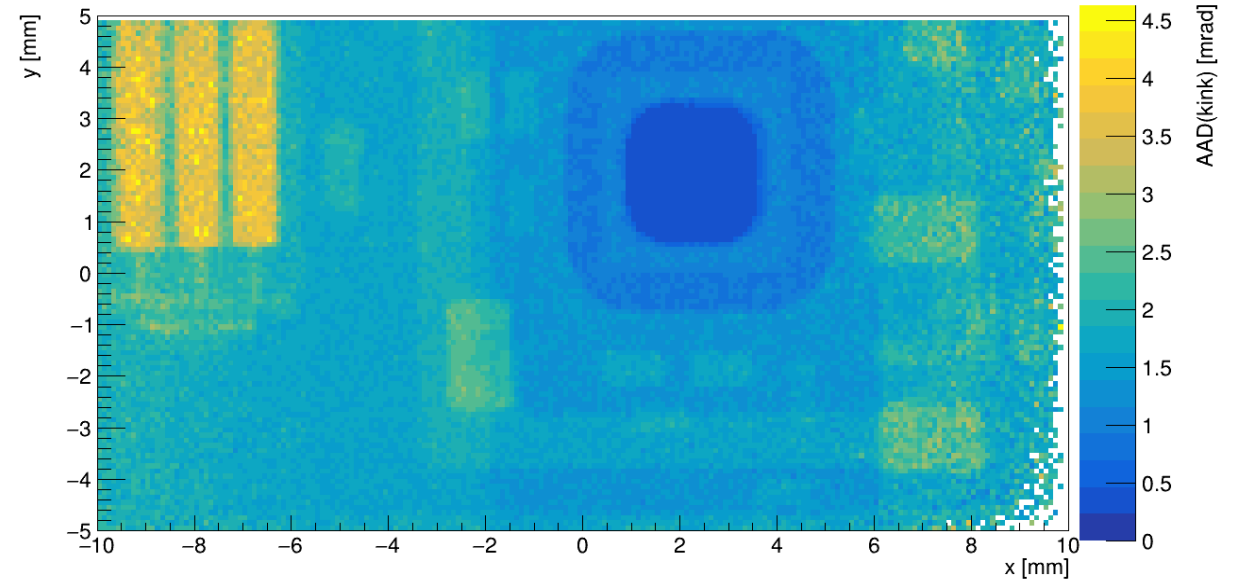
MBI for Alignment to the VETO Area



hitmap

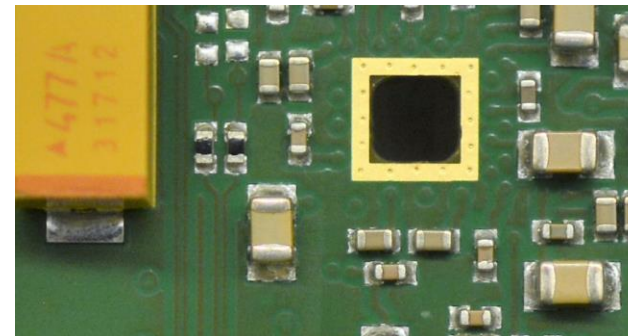


Material Budget Image (AAD)



Plastic scintillator with a hole used as VETO for Trigger

- Anticoincidence with other scintillators
- Trigger only in a ROI slightly larger than DUT
- Allows to save disk space and maximize yield



Material budget image for DUT alignment

Corryvreckan modules:
[TrackingMultiplets]
[AnalysisMaterialBudget]

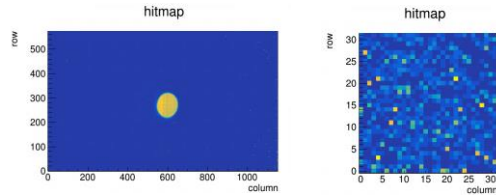
Analysis Chain

Using Corryvreckan



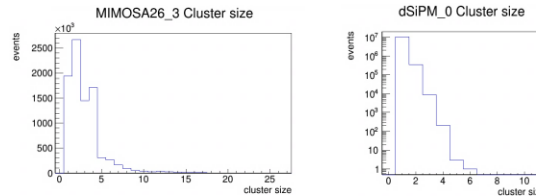
Data Decoding

Raw Telescope & dSiPM data are **decoded** into an accessible format



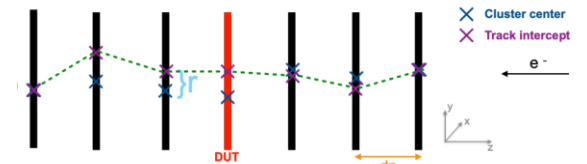
Clustering

Clusters of hits in the reference telescope and DUT are identified



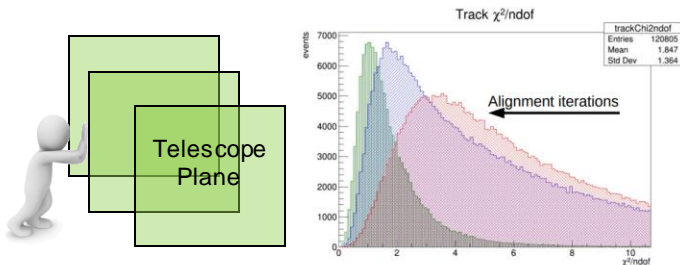
Tracking

Tracks are reconstructed using telescope clusters + spatial & temporal cuts



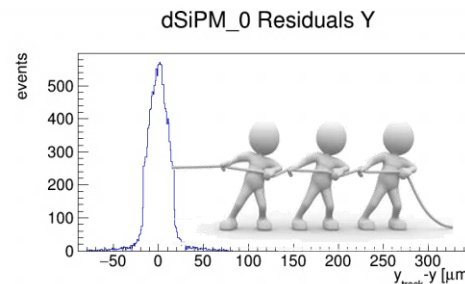
Telescope Alignment

Software **translations and rotations** of the **telescope planes** are performed



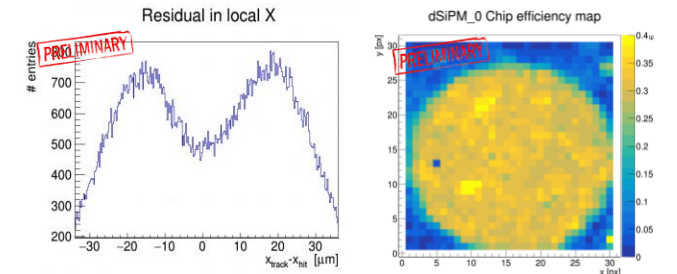
dSiPM Alignment

Translations and rotations of the **DUT** are performed to minimize unbiased residuals





DUT Association & analysis

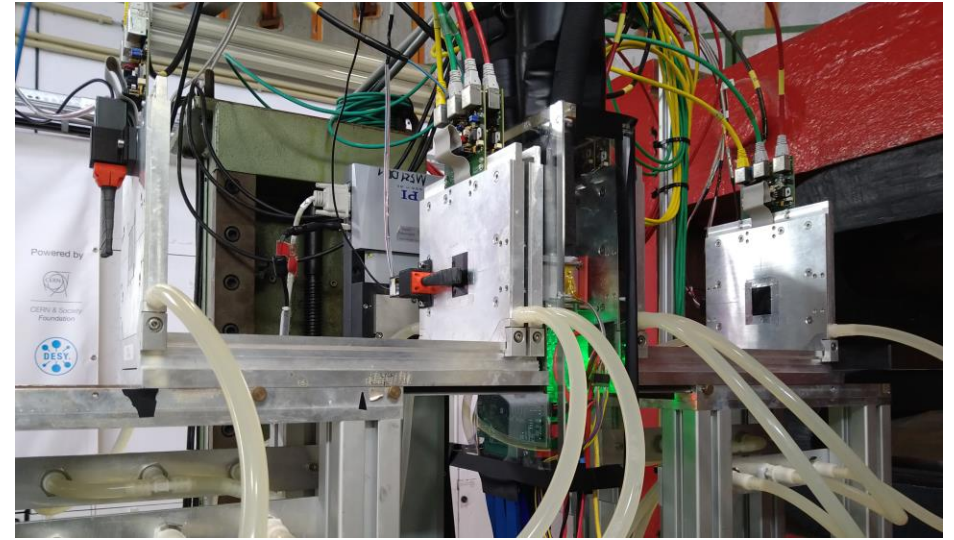
DUT clusters are associated with tracks & its **MIP detection response** is analyzed



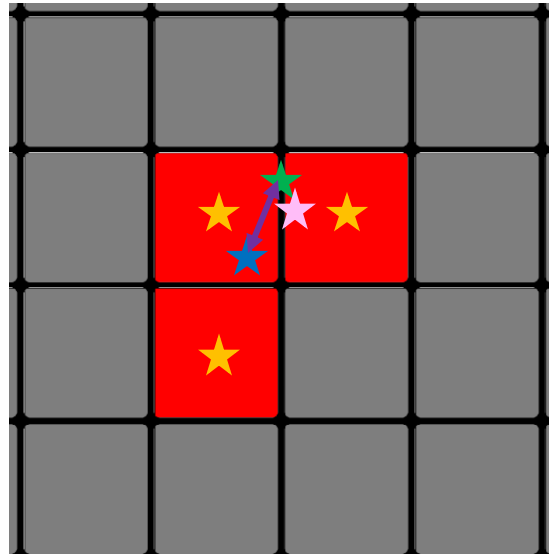
TestBeam data reconstruction

Using Corryvreckan Framework

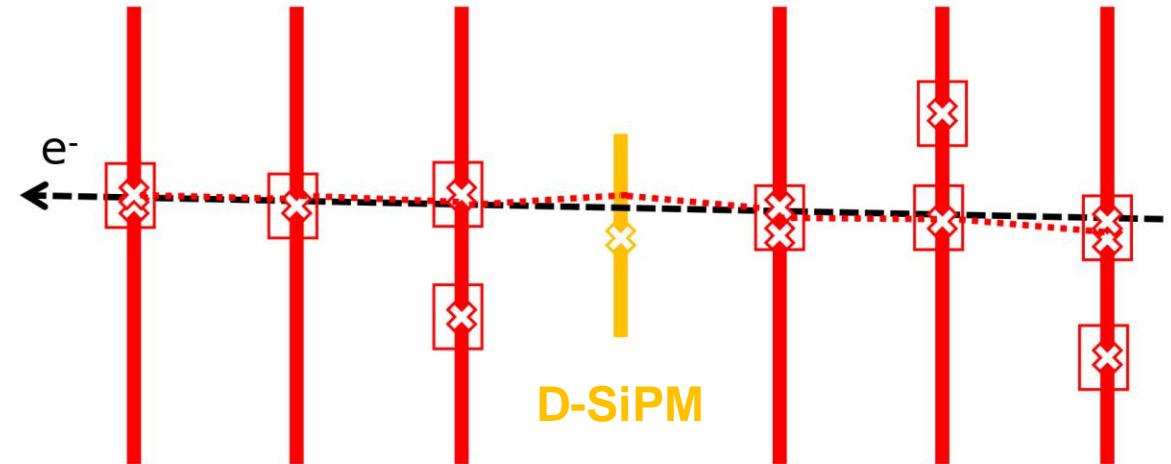
- Corryvreckan use hit  (pixels above threshold) and Clusters  (groups of adjacent hits) to reconstruct particle trajectories.
- DUT response is then investigated on associated events



SiPM-IC testbeam setup



- Real Track
- Hit
- Cluster
- Cluster center
- Reconstructed Track
- Residuals



MIMOSA 26

<http://cern.ch/corryvreckan>

dSiPM + LYSO Sr-90 Data

Random Selection (100, 200, 500 from the top)

Overvoltage ~ 1.5

Temperature on Chip $\sim 25\text{C}$

